



2N7002A

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
60V	6Ω @ $V_{GS} = 5V$	200mA	

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability.
- https://www.diodes.com/quality/product-definitions/

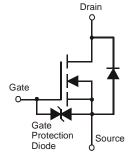
Mechanical Data

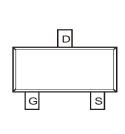
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)





SOT23





Top View

Equivalent Circuit

Top View Pin-Out

Ordering Information (Note 4)

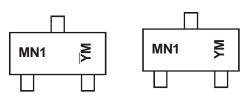
Part Number	Case	Packaging
2N7002A-7	SOT23	3,000/Tape & Reel
2N7002A-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



 $\begin{array}{l} MN1 = Product\ Type\ Marking\ Code \\ \underline{YM} = Date\ Code\ Marking\ for\ SAT\ (Shanghai\ Assembly/\ Test\ site) \\ \overline{YM} = Date\ Code\ Marking\ for\ CAT\ (Chengdu\ Assembly/\ Test\ site) \\ Y\ or\ \overline{Y} = Year\ (ex:\ A=2013) \\ M = Month\ (ex:\ 9=September) \end{array}$

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

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Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $Steady State$ $T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$		I _D	180 130 115	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	220 160 140	mA	
Maximum Continuous Body Diode Forward Current	(Note 6)	I _S	0.5	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%))	I _{DM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Dower Dissination	(Note 5)		370	mW	
Total Power Dissipation	(Note 6)	P _D	540		
Thermal Resistance, Junction to Ambient	(Note 5)	Б	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R ₀ JC	91		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

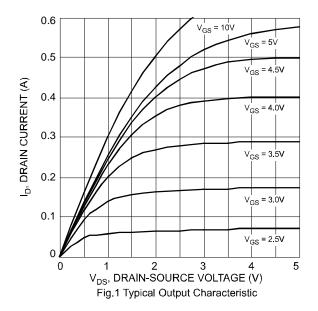


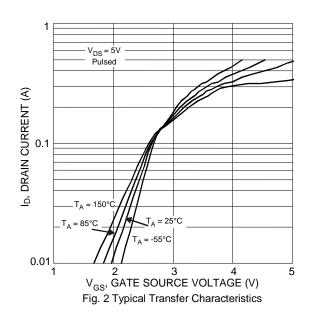
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						•	
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$		I _{DSS}	_	_	1.0 500	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(th)}	1.2	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C	R _{DS(ON)}	_	3.5	6	0	V _{GS} = 5.0V, I _D = 0.115A
	@ $T_J = +125$ °C			3.0	5	Ω	$V_{GS} = 10V, I_D = 0.115A$
Forward Transconductance		g FS	80	_	_	mS	V _{DS} = 10V, I _D = 0.115A
DYNAMIC CHARACTERISTICS (Note	8)						
Input Capacitance		Ciss	_	23	_	pF	
Output Capacitance		Coss	_	3.4	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}	_	1.4	_	pF	
Gate Resistance		R _G	_	260	400	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (No	ote 8)						
Turn-On Delay Time		t _{D(ON)}	_	10	_	ns	$V_{DD} = 30V, I_D = 0.115A, R_L = 150\Omega,$
Turn-Off Delay Time		t _{D(OFF)}	_	33	_	ns	$V_{GEN} = 10V, R_{GEN} = 25\Omega$

Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







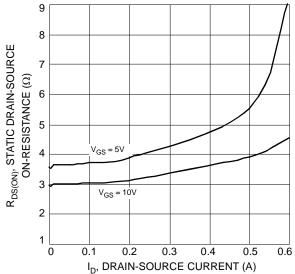


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

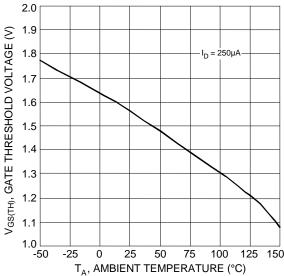


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

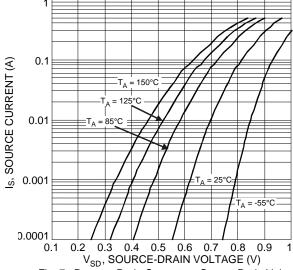


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

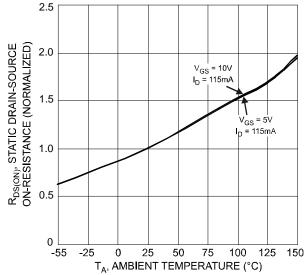
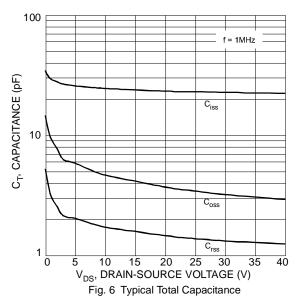


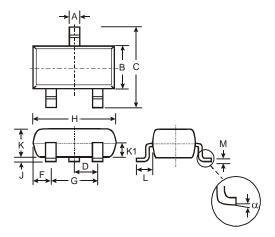
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





Package Outline Dimensions

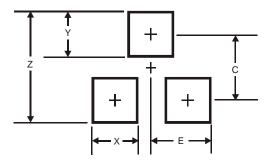
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Η	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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